Optical properties of ternary alloys MgZnO in infrared spectrum

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Abstract. Properties of thin films of ternary alloys MgₓZn₁₋ₓO on the optically-anisotropic Al₂O₃ substrates in the area of “residual rays” of film and substrate are first investigated using the method of infrared spectroscopy and dispersion analysis of reflection coefficients. It was established that the changes in thickness of film and content of Mg substantially deform the spectrum of reflection in the area of “residual rays” of film and substrate, decrease the reflectivity. First by means of Kramers–Kronig relations with use of the method of dispersion analysis of infrared reflection spectra, the static dielectric constant of MgₓZn₁₋ₓO structure has been obtained at different values of x, when orientation is E⊥C. It was ascertained that the MgₓZn₁₋ₓO/Al₂O₃ structures are well modelled when using the mutually agreed parameters, obtained earlier for the single crystals of magnesium oxide, zinc oxide and leicsapphire at the orientation E⊥C. It was theoretically shown and experimentally grounded the assurance of the obtained optical parameters of MgₓZn₁₋ₓO films by the non-destructive method of infrared spectroscopy in the wide spectral range. The obtained results are well agreed with the literature data.

Keywords: optical properties, ternary alloys, MgZnO, infrared spectrum, infrared spectroscopy, dispersion analysis of reflection coefficients.

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1. Introduction

Today zinc oxide (ZnO), due to its high radiation, chemical and thermal stability, is an enough applicable semiconductor in acousto-, opto- and nanoelectronics [1-4]. Zinc oxide is especially actual when making the transparent film electrodes for solar cells [5], and high binding energy of excitons (60 meV) in ZnO promotes laser generation at room temperature [1, 2]. A bandgap (E₉ = 3.37 eV) allows to use ZnO for creation of detectors and filters in the ultraviolet range. In addition, zinc oxide found wide application for manufacturing gas sensors, light-emitting diodes, varistors, photocatalizators for cleaning water and air etc. [5]. In its turn, ZnO films on Si and CdTe substrates have considerably subzero prime price and are perspective material for creation of antireflective, current-carrying layers in solar cells of large area [5-7].

Next to ZnO, there is another widely used material that has excellent characteristics in application, it is magnesium oxide (MgO). MgO is one of the most widespread natural minerals that is crystallized in the rocky structure of Earth at any pressures and temperatures [8]. The crystals of MgO are transparent, fire and explosion undangerous, practically insoluble in water, however soluble in muriatic, sulphuric and vinegar acids. MgO has a high temperature of melting 2800 °C, that is why it is widely used as substrate material for the processes of growing thin films in modern microelectronic and optronic devices [8, 9].

In the works by Ye.F. Venger and coauthors [10-12], the analysis of both ZnO and MgO compounds was performed, which is a result of that ZnO is compound of semiconductor of family A²B₆, and MgO is usually examined as a widegap semiconductor close to dielectric, as its bandgap is 8.2 eV. MgO has a cubic structure like NaCl type. However, in spite of the fact that ZnO and MgO have different crystalline structures, zinc oxide has a hexagonal crystalline structure (wurtzite), and magnesium oxide – the cubic one, these two materials can be connected with each other, forming the MgₓZn₁₋ₓO compound. The obtained ternary compound extends the limits of their application. First it was described in the works Kawasaki et al. [13], where the possibility to change optical and electrophysical properties of ternary alloys MgₓZn₁₋ₓO by changing the bandgap in ZnO films was shown.

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Thus, for the increase of $E_r$, it needs to use the elements of the second group that are placed higher in the Mendeleyev table, for example Mg [13], and for decrease – elements that are below, for example Cd [14]. In the dependence on the relative concentrations of Mg and Zn, ternary alloys Mg$_2$Zn$_{1-x}$O may have both hexagonal crystalline structure (wurtzite) and the cubic one. In the work [15], it was shown that at $x < 0.3$ hexagonal crystalline structure is inherent to Mg$_2$Zn$_{1-x}$O and bandgap changes from 3.4 up to 3.8 eV, which allows to use them for manufacturing substances for optoelectronics with the range of wavelengths from red up to deep ultraviolet. At $x > 0.3$, cubic crystalline structure is inherent to Mg$_2$Zn$_{1-x}$O. Thus, due to the unique properties (high photo-response, high quantum yield of photo- and cathodoluminescence, presence of pyro- and piezoelectric effects etc.), Mg$_2$Zn$_{1-x}$O films belong to materials that provide a base for the various optoelectronic devices that were created with the use of volume and surface waves. Advantage of the devices based on Mg$_2$Zn$_{1-x}$O is their diminutiveness, high efficiency of operation in a wide frequency range, use in optics and optoelectronics, in light-emitting diodes for the ultraviolet spectral region, in laser diodes or sensors, as well as possibility of integration with other microelectronic elements [15-20].

However, data about study of undoped and strong doped films of MgZnO at the concentrations of electrons from $10^{16}$ to $5 \times 10^{18}$ cm$^{-3}$ on the Al$_2$O$_3$ dielectric substrates by using the method of infrared spectroscopy of external reflection in the area of “residual rays” of film and substrate at the orientations $E\perp C$ and $E\parallel C$ in the literature is lighted up limit enough.

Attractiveness to research the ternary alloys Mg$_2$Zn$_{1-x}$O with the range of Mg$^{2+}$ from 0 to 30% is keeping the hexagonal lattice and displaying the optically-anisotropic properties in the infrared spectrum. At $x > 30\%$, the cubic lattice of the considered ternary alloys is typical.

The aim of this work was to study optical properties of films of ternary alloys Mg$_2$Zn$_{1-x}$O on the optically-anisotropic Al$_2$O$_3$ substrates by means of the method of spectroscopy of external infrared reflection.

2. Samples and the method for measuring

Synthesis of the films was performed using the industrial modernized setup BY-1A and possibilities of computer controlling the technological parameters (temperature, pressure, position of shutters etc.). It was shown that the developed software allowed the operator to force setup into an operation mode, to synthesize automatically thin films (at the set temperature conditions, thickness, concentrations of free charge carriers etc.) and remove of setup from operation mode. The rate of Mg$_2$Zn$_{1-x}$O film growth at $x < 20\%$ on the Al$_2$O$_3$ substrates was 0.1...0.15 µm/hour. The thickness of films was determined by means of the interferometer MИИ-4 and changed from 0.1 up to 10 µm.

As a substrate for growing monocrystalline zinc oxide layers, single crystals of leicsapphire were used. In the hexagonal Al$_2$O$_3$ single crystals there is a plane that is perpendicular to $z$-axis that is designated (0001), and in rhombohedral ones – (111) [21]. From the possible variety of sapphire orientations for epitaxial growing the ZnO thin films, advantage was given to orientations with the densely packed planes (0001), (1102), (1120), (1012), on which it is possible to grow the layers with high mobility of charge carriers [21, 22].

By means of the spectrophotometer HKC-29M and the use of facility HIP-22 at $T = 300$ K, the spectra of external reflection of Al$_2$O$_3$ substrate were measured within the range 400...1200 cm$^{-1}$. A mathematical model with the additive and phenomenological contribution of oscillators to permittivity was presented. The spectra of infrared reflection for Mg$_2$Zn$_{1-x}$/Al$_2$O$_3$, which allows to perform the dispersion analysis of spectra with account of orientation inherent to optical axes in film and substrate.

3. Theory and discussion of results

Let us consider the structure of Mg$_2$Zn$_{1-x}$/Al$_2$O$_3$ that consists of absorptive film on the absorptive semi-infinite substrate. The area of “residual rays” of ternary alloy MgZnO comprises the range from 400 up to 1000 cm$^{-1}$. In the monographs [10, 25], there was shown the possibility to model semiconductor or dielectric structure that consists of optically-anisotropic (isotropic) film on the optically-anisotropic (isotropic) substrate, when using the multisimilometric mathematical model for the orientations $E\perp C$ and $E\parallel C$. In addition, calculation of spectra of infrared reflection from the Mg$_2$Zn$_{1-x}$/Al$_2$O$_3$ surface was carried out after formulas that take into account interaction of infrared emission with the phonon and plasma subsystems of film and semi-infinite substrate of Al$_2$O$_3$ for the case $E\perp C$ and $E\parallel C$:

$$\frac{RT(\nu)}{\rho} = \frac{q_1^2 + h_1^2}{\exp(q_1 - h_1)} \exp(q_2 + h_2) + \frac{q_2^2 + h_2^2}{\exp(q_1 - h_1)} + \frac{q_3^2 + h_3^2}{\exp(q_1 - h_1)} + \frac{q_4^2 + h_4^2}{\exp(q_1 - h_1)} + \frac{q_5^2 + h_5^2}{\exp(q_1 - h_1)}$$

where

$$A = 2(q_1 q_2 + h_1 h_2), \quad B = 2(q_1 h_2 + q_2 h_1), \quad C = 2(q_1 q_2 + h_2 h_2), \quad D = 2(q_1 q_2 + h_2 h_2), \quad q_1 = n_1^2 - n_2^2 - k_2^2, \quad q_2 = n_2^2 - n_3^2 + k_2^2, \quad q_3 = n_3^2 - n_2^2 + k_2^2, \quad q_4 = n_1^2 + n_3^2 + k_2^2, \quad q_5 = n_1^2 + n_3^2 + k_2^2,$$

$$h_1 = \frac{2n_2 k_3}{n_1 + n_2} + k_2, \quad h_2 = \frac{2n_2 k_3}{n_2 + n_3} + k_2, \quad h_3 = \frac{2n_2 k_3}{n_1 + n_3} + k_2, \quad h_4 = \frac{2n_2 k_3}{n_2 + n_3} + k_2, \quad h_5 = \frac{2n_2 k_3}{n_1 + n_3} + k_2,$$

$$\gamma_1 = \frac{4\pi \alpha d}{\lambda}, \quad \delta_2 = \frac{4\pi \alpha d}{\lambda}, \quad (n_1, n_2, n_3)$$

(n$_1, n_2, n_3$ are the indexes of refraction; k$_1, k_2, k_3$ – indexes of absorption inherent to air, film with the thickness $d$ and semi-infinite substrate, respectively).
Table 1. Parameters of Al₂O₃ single crystal for calculation of $R(\nu)$ at the orientation E.L.C.

<table>
<thead>
<tr>
<th>$\nu_{TO}$, cm$^{-1}$</th>
<th>$\Delta \varepsilon_i$</th>
<th>$\gamma_i/\nu_{TO}$</th>
</tr>
</thead>
<tbody>
<tr>
<td>384</td>
<td>0.2</td>
<td>0.015</td>
</tr>
<tr>
<td>442</td>
<td>2.8</td>
<td>0.01</td>
</tr>
<tr>
<td>571</td>
<td>3.1</td>
<td>0.2</td>
</tr>
<tr>
<td>634</td>
<td>0.2</td>
<td>0.02</td>
</tr>
</tbody>
</table>

Table 2. The mutually agreed volume parameters of single crystals of magnesium oxide [12, 26] and zinc oxide [10] ($T = 293$ K).

<table>
<thead>
<tr>
<th>Material</th>
<th>$\varepsilon_0$</th>
<th>$\varepsilon_\infty$</th>
<th>$\nu_{TO}$, cm$^{-1}$</th>
<th>$\nu_{LO}$, cm$^{-1}$</th>
</tr>
</thead>
<tbody>
<tr>
<td>ZnO (E.L.C)</td>
<td>8.1</td>
<td>3.95</td>
<td>412</td>
<td>591</td>
</tr>
<tr>
<td>ZnO (E.I.C)</td>
<td>9.0</td>
<td>4.05</td>
<td>380</td>
<td>570</td>
</tr>
<tr>
<td>MgO (E.L.C)</td>
<td>2.98</td>
<td>9.39</td>
<td>416</td>
<td>738</td>
</tr>
</tbody>
</table>

Fig. 1. Calculated spectra of infrared reflection $R(\nu)$ of single crystals MgO (1), ZnO (2), Al₂O₃ (3) at the orientation E.L.C.

Calculation of $n_2$ and $n_3$ was performed as based on the model of permittivity with additive contribution of active optical phonons $\nu_{TO}$ and plasmons $\nu_p$ [10, 25]:

$$\varepsilon_{MgZnO}(\nu) = \varepsilon_{\infty}(\nu) + j\varepsilon_2(\nu) =$$

$$= \sum_{i=1}^{3} \frac{\Delta \varepsilon_i \nu_{TO}^2}{\nu_{TO}^2 - \nu^2 - j \nu \gamma_i} - \sum_{i=1}^{3} \frac{\varepsilon_{\infty} \nu_p^2}{\nu^2 - j \nu \gamma_p}$$

where $\nu_{LO}, \nu_{TO}$ are the frequencies of longitudinal and transversal optical phonons; $\gamma_i$ is the fading coefficient of optical phonon; $\nu_p$ and $\gamma_p$ are fading coefficient and frequency of plasmon resonance; and $i = 1...3$ are indexes of oscillators in the film. When modeling the Al₂O₃ substrate, we used the dependence of permittivity of sapphire on frequency for E.L.C [10]:

$$\varepsilon(\nu) = \varepsilon_{\infty} + \sum_{i=1}^{4} \frac{\Delta \varepsilon_i \nu_{TO}^2}{\nu_{TO}^2 - \nu^2 + j \nu \gamma_i} ,$$ (2)

where $\varepsilon_{\infty}$ is a high-frequency permittivity of sapphire for the orientation E.L.C (it was accepted to be equal to 3.2); $\Delta \varepsilon_i$ is the force of $i$-th oscillator; $\nu_{TO}$ is frequency of transversal optical fading of $i$-th oscillator; $\gamma_i$ is the value of fading coefficient of $i$-th oscillator. The data used for the calculation of spectra $R(\nu)$ from the Al₂O₃ surface were listed in Table 1.

In Fig. 1, the spectra of infrared reflection of single crystals of magnesium oxide (curve 1), zinc oxide (curve 2) and aluminium oxide (curve 3) at the orientation of E.L.C are presented, which were measured with account of the data [10, 12]. For modeling the spectra of infrared reflection, the mathematical expressions of multioscillometric mathematical model (1) and (2) were used. The mutually agreed parameters of oscillators for the indicated single crystals are presented accordingly in Tables 1 and 2.

The area of “residual rays” of MgO, ZnO single crystals is located within the range 400 to 1000 cm$^{-1}$, which complicates task of exact determination of influence of optical parameters on characteristics of the reflection spectrum for every separately taken material. In addition, zinc oxide is a semiconductor where optical and electrophysical properties influence on the spectrum of reflection depending on the degree of doping the single crystal and type of charge carriers. It should be noted that each single crystal of presented in Fig. 1 ones was thoroughly studied by the authors earlier [10, 12].

To study the influence of properties inherent to optically-isotropic film on the spectrum of infrared reflection, the double-layer ZnO/Al₂O₃ and MgO/Al₂O₃ structures were used.

In Fig. 2, we show the experimental (points 1) and theoretical (curve 2) results of research of monocrystalline films of zinc oxide with the thickness 0.1$\mu$m at E.L.C by the methods of spectroscopy of infrared reflection. Experimental spectra were measured using the spectrometer IKC-29M with the facility ИПО-22 (taking into account the method described in [10]).
within the range 400 to 1400 cm\(^{-1}\). The spectra were registered in the polarized irradiation at the orientation of the electric vector of \(\text{E.L.C.}\) of \(\text{Al}_2\text{O}_3\) crystal. The curve 1 (points) corresponds to the experimental values of \(R(v)\) of \(\text{ZnO/Al}_2\text{O}_3\) structure with the thickness of \(\text{ZnO}\) layer \(d = 0.1\ \mu\text{m}\). The calculated spectrum from the \(\text{ZnO/Al}_2\text{O}_3\) surface was measured at parameters for \(\text{ZnO}\) film, which were presented in signatures to Fig. 2 and data of Tables 1 and 2. As it is evident from the figure, in the spectrum there are minima at the frequencies 475, 505, 620 cm\(^{-1}\). In the absence of \(\text{ZnO}\) film, minima in the \(\text{Al}_2\text{O}_3\) spectra are at the frequencies 390, 420, 489, 633 cm\(^{-1}\) (Fig. 1, curve 3).

It is shown in theory that when the thickness is less than 80 nm, the shape of the spectrum \(R(v)\) is defined mainly by \(\text{Al}_2\text{O}_3\) substrate, and the zinc oxide layer of the thickness 10 \(\mu\text{m}\) forms the spectrum of reflection of semi-infinite zinc oxide single crystal. The change in sample orientation in the polarized radiation did not change practically the shape of spectrum \(R(v)\), which testified that the orientation of the textured \(\text{ZnO}\) layers is the same as in the substrate. The curve 3 of Fig. 2 was calculated for free film of zinc oxide with the thickness \(d = 0.1\ \mu\text{m}\). The peak of the curve is at the frequency 412 cm\(^{-1}\) at \(R(v) = 0.47\).

In Fig. 3, the spectra of infrared reflection of \(\text{ZnO/Al}_2\text{O}_3\) structure at the orientation \(\text{E.L.C.}\) are presented. The curve 1 corresponds to \(R(v)\) when the thickness of \(\text{ZnO}\) layer \(d = 0.5\ \mu\text{m}\). In the spectrum, there is a minimum of reflection at the frequency 510 cm\(^{-1}\) (curve 1) and two bends near 430 and 600 cm\(^{-1}\), while when modeling the \(\text{ZnO/Al}_2\text{O}_3\) structure, minima of \(R(v)\) are at the frequencies 325, 427, 491 and 515 cm\(^{-1}\) (curve 2).

The maxima of \(R(v)\) are located at the frequencies 432 and 600 cm\(^{-1}\), here a curve fluently diminishes \(R(v)\) into the area of higher frequencies. The calculated \(R(v)\) (curve 2) is determined for the following parameters of \(\text{ZnO}\) layer: \(d = 0.5\ \mu\text{m}\), \(\nu_{\text{TO}} = 412\ \text{cm}^{-1}\), \(\gamma_{\text{L}} = 15\ \text{cm}^{-1}\), \(\nu_{\text{L}} = 400\ \text{cm}^{-1}\), \(\gamma_{\text{L}} = 870\ \text{cm}^{-1}\); 3 – calculation of \(R(v)\) for \(\text{ZnO}\) film (without substrate).

As seen from Fig. 3, the presence in \(\text{ZnO}\) films of free charge carriers (electrons) of the order of \(n_0 = \times 10^{18}…\times 10^{19}\ \text{cm}^{-3}\) substantially deforms the spectrum of reflection in the area between 400 and 1000 cm\(^{-1}\). The reflection coefficient at the frequency 680 cm\(^{-1}\) diminishes to 0.8 at the presence of the minimum 0.4 at the frequency 510 cm\(^{-1}\).

The change of position of the doped zinc oxide films on \(\text{Al}_2\text{O}_3\) substrate in the plane \(xy\) practically does not change the shape of \(R(v)\) spectrum, which testifies isotropy of optical and electrophysical properties of the investigated system. In addition, it is possible to assert that the optical axis of the textured layers of zinc oxide and sapphire is normal to the plane of \(xy\) (\(C\perp xy\)).

For the concentration of free charge carriers \(n_0 > 5 \times 10^{17}\ \text{cm}^{-3}\), there is decreasing the reflection coefficient at the frequencies higher than 700 cm\(^{-1}\). On the basis of analysis of the studied \(\text{ZnO/Al}_2\text{O}_3\) structures, it is found that in our case the zinc oxide layers have the following values of the electron concentration \(n_0 = (1.6…2.8) \times 10^{18}\ \text{cm}^{-3}\), mobility \(\mu = 1.1…3.1\ \text{cm}^2/(\text{V} \cdot \text{s})\) and conductivity within the range \(\sigma_0 = 110…200\ \text{Ohm}^{-1}\cdot\text{cm}^{-1}\).

In Fig. 4, the calculated dependences \(R(v)\) of \(\text{MgO/Al}_2\text{O}_3\) structure on the thickness of magnesium oxide film are presented. The curves 2 to 4 correspond to the thickness 0.1, 0.25, 0.5 \(\mu\text{m}\) at \(\gamma_{\text{L}} = 12\ \text{cm}^{-1}\). The increase of the film thickness to 0.5 \(\mu\text{m}\) results in the considerable increase of \(R(v)\) values in the area close to 500 cm\(^{-1}\). Within the frequency range from 450 to 580 cm\(^{-1}\), there is a change of \(R(v)\) from 0.18 for \(d = 0.1\ \mu\text{m}\) (curve 2) to 0.45 for \(d = 0.5\ \mu\text{m}\) (curve 4). The curve 1 was calculated for the \(\text{Al}_2\text{O}_3\) single crystal for parameters indicated in Table 1. The change of film thickness from 0.1 to 0.5 \(\mu\text{m}\) at the unchanged mutually agreed parameters for magnesium oxide is not accompanied by changes in the spectrum of reflection within the range 600…1200 cm\(^{-1}\).
Table 3. Parameters of the investigated samples.

<table>
<thead>
<tr>
<th>Sample</th>
<th>( \varepsilon_\infty )</th>
<th>( \varepsilon_0 )</th>
<th>( \nu_{TO} ), cm(^{-1})</th>
<th>( \nu_{LO} ), cm(^{-1})</th>
<th>( \Delta S_1 )</th>
<th>( \gamma_T ), cm(^{-1})</th>
<th>( \gamma_{LO} ), cm(^{-1})</th>
<th>( \gamma_{TO} ), cm(^{-1})</th>
<th>( \gamma_\infty ), cm(^{-1})</th>
</tr>
</thead>
<tbody>
<tr>
<td>( \text{Mg}<em>{0.4} \text{Zn}</em>{0.6} \text{O}/\text{Al}_2\text{O}_3 )</td>
<td>3.3</td>
<td>7.06</td>
<td>385</td>
<td>386</td>
<td>1.5</td>
<td>5.0</td>
<td>436</td>
<td>636</td>
<td>15</td>
</tr>
<tr>
<td>( \text{Mg}<em>{0.4} \text{Zn}</em>{0.6} \text{O}/\text{Al}_2\text{O}_3 )</td>
<td>3.1</td>
<td>7.88</td>
<td>389</td>
<td>395</td>
<td>0.8</td>
<td>9.0</td>
<td>447</td>
<td>702</td>
<td>7.0</td>
</tr>
</tbody>
</table>

Fig. 5. Calculated spectra \( R(\nu) \) of the \( \text{Mg}_x \text{Zn}_{1-x} \text{O}/\text{Al}_2\text{O}_3 \) structure: \( 1 - x = 0.47; 2 - x = 0.60 \) at \( d = 2 \) \( \mu \)m.

Fig. 5 shows the dependence of \( R(\nu) \) of the \( \text{Mg}_x \text{Zn}_{1-x} \text{O}/\text{Al}_2\text{O}_3 \) structure at \( x = 0.47 \) (curve 1) and \( x = 0.6 \) (curve 2) with the film thickness 2 \( \mu \)m. This calculation was performed using the Kramers–Kronig relations and data [25] and presented in Table 3. The values of static dielectric constant listed in Table 3 were determined by the authors of this paper with the use of the Lidden–Sax–Teller relation. The obtained results are well agreed with the data presented in the plot of the work [25]. As it is obvious from comparison of the curves 1 and 2, the increase of Mg content in the \( \text{Mg}_x \text{Zn}_{1-x} \text{O}/\text{Al}_2\text{O}_3 \) structure from \( x = 0.47 \) (curve 1) up to 0.60 (curve 2) is accompanied by changes in the spectrum of external reflection at the frequencies of “residual rays” of zinc oxide and magnesium oxide.

The most essential changes are observed accordingly in the ranges 650...750 and 900...1100 cm\(^{-1}\), which is caused by the frequencies of transversal and longitudinal optical phonons in the investigated materials. In turn, it indicates the possibility to develop practical modulators for the infrared spectral range.

Fig. 6 shows the dependence of \( R(\nu) \) of the \( \text{Mg}_x \text{Zn}_{1-x} \text{O}/\text{Al}_2\text{O}_3 \) structure on the thickness of \( \text{Mg}_x \text{Zn}_{1-x} \text{O} \) film. The curves 1 to 3 correspond to the thickness 1, 0.5, 0.25 \( \mu \)m. The calculation was performed with the parameters presented in Table 3. As seen from the figure, the increase of film thickness from 0.25 to 1 \( \mu \)m results in the considerable increase of \( R(\nu) \) in the whole range of “residual rays”. At the frequency 525 cm\(^{-1}\), there is a change of \( R(\nu) \) from 0.59 for \( d = 0.25 \) to 0.92 for \( d = 1 \) \( \mu \)m, for the frequency 726 cm\(^{-1}\) the increase of \( R(\nu) \) is observed from 0.63 for \( d = 0.25 \) \( \mu \)m to 0.77 for \( d = 1 \) \( \mu \)m. Most essential changes from 0.08 to 0.4 were registered at the frequency 940 cm\(^{-1}\).

4. Conclusions

Thus, obtained in this work by using the method of infrared spectroscopy of external reflection are optical characteristics of thin films of ternary alloys \( \text{Mg}_x \text{Zn}_{1-x} \text{O} \) on the \( \text{Al}_2\text{O}_3 \) dielectric substrate in the area of “residual rays” of film and substrate. It has been shown that the changes in film thickness and content of Mg substantially deform the spectrum of reflection in the area of “residual rays” of film and substrate, decrease reflection ability. The computer experiment of infrared spectra allowed to determine the static dielectric constant of \( \text{Mg}_x \text{Zn}_{1-x} \text{O} \) structure at the different \( x \) values for the orientation ELC. It is found that the \( \text{Mg}_x \text{Zn}_{1-x} \text{O}/\text{Al}_2\text{O}_3 \) structures is well modeled with using the mutually agreed parameters presented in Tables 1 to 3, for the single crystals of magnesium oxide, zinc oxide and leicosapphire for the orientation ELC, which confirms perspectives of the non-destructive method of infrared spectroscopy for determination of optical characteristics of films of ternary alloys and rate of their texturing.

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References


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